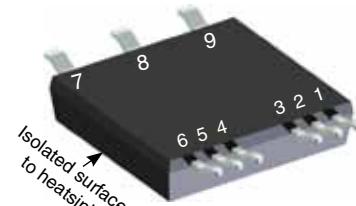
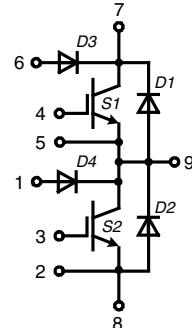


XPT IGBT phaseleg

ISOPLUS™

Surface Mount Power Device

I_{C25} = 63 A
V_{CES} = 1200 V
V_{CE(sat)} typ = 1.85 V



E72873

IGBTs S1, S2

Symbol	Conditions	Maximum Ratings		
V _{CES}	T _{VJ} = 25°C to 150°C	1200	V	
V _{GES}		±20	V	
I _{C25}	T _C = 25°C	63	A	
I _{C80}	T _C = 80°C	45	A	
I _{CM}	V _{GE} = 15 V; R _G = 27 Ω; T _{VJ} = 125°C	105	A	
V _{CEK}	RBSOA, clamped inductive load; L = 100 μH	V _{CES}		
t _{sc} (SCSOA)	V _{CE} = 900 V; V _{GE} = ±15 V; R _G = 27 Ω; T _{VJ} = 125°C none repetitive	10	μs	
P _{tot}	T _{VJ} = 25°C	230	W	

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)		
		min.	typ.	max.

V _{CE(sat)}	I _C = 35 A; V _{GE} = 15 V; T _{VJ} = 25°C T _{VJ} = 125°C		1.85 2.2	2.15	V
V _{GE(th)}	I _C = 1.5 mA; V _{GE} = V _{CE}	5.4		6.5	V
I _{CES}	V _{CE} = V _{CES} ; V _{GE} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C		0.25	0.15	mA mA
I _{GES}	V _{CE} = 0 V; V _{GE} = ± 20 V			200	nA
t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off}	Inductive load; T _{VJ} = 125°C V _{CE} = 600 V; I _C = 35 A V _{GE} = ±15 V; R _G = 27 Ω		70 40 250 100 3.8 4.1		ns ns ns ns mJ mJ
C _{ies} Q _{Gon}	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz V _{CE} = 600 V; V _{GE} = 15 V; I _C = 35 A		tbd 107		pF nC
R _{thJC} R _{thJH}	with heatsink compound (IXYS test setup)		0.75	0.55 0.95	K/W K/W

Features

- **XPT IGBT**
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- **Sonic™ diode**
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- **V_{CEsat} detection diode**
 - integrated into package
 - very fast diode
- **Package**
 - isolated back surface
 - low coupling capacity between pins and heatsink
 - PCB space saving
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability

Applications

- **Phaseleg**
 - buck-boost chopper
- **Full bridge**
 - power supplies
 - induction heating
 - four quadrant DC drives
 - controlled rectifier
- **Three phase bridge**
 - AC drives
 - controlled rectifier

Diodes D1, D2

Symbol	Conditions	Maximum Ratings			
I _{F25}	T _C = 25°C	40	A		
I _{F80}	T _C = 80°C	27	A		
Symbol	Conditions	Characteristic Values			
		(T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V _F	I _F = 35 A	T _{VJ} = 25°C T _{VJ} = 125°C	2.1 2.1	2.4	V
I _{RM} t _{rr} E _{rec}	I _F = 35 A; R _G = 27 Ω; T _{VJ} = 125°C V _R = 600 V; V _{GE} = -15 V		30 350 tbd		A ns mJ
R _{thJC} R _{thJH}	per diode with heatsink compound (IXYS test setup)		1.2	0.9 1.5	K/W K/W

Diodes D3, D4

Symbol	Conditions	Maximum Ratings			
V _R	T _C = 25°C to 150°C	1200			
Symbol	Conditions	Characteristic Values			
		(T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V _F	I _F = 1 A	T _{VJ} = 25°C T _{VJ} = 125°C	1.7 1.5	2.2	V
I _R	V _R = 1200 V	T _{VJ} = 25°C T _{VJ} = 125°C		2 30	μA μA
I _{RM} t _{rr}	I _F = 1 A; di _F /dt = -100 A/μs; T _{VJ} = 25°C V _R = 100 V; V _{GE} = 0 V		2.3 40		A ns

Component

Symbol	Conditions	Maximum Ratings		
T _{VJ}		-55...+150 °C		
T _{stg}		-55...+125 °C		
V _{ISOL}	I _{ISOL} ≤ 1 mA; 50/60 Hz	2500	V~	
F _c	mounting force	40 ... 130	N	

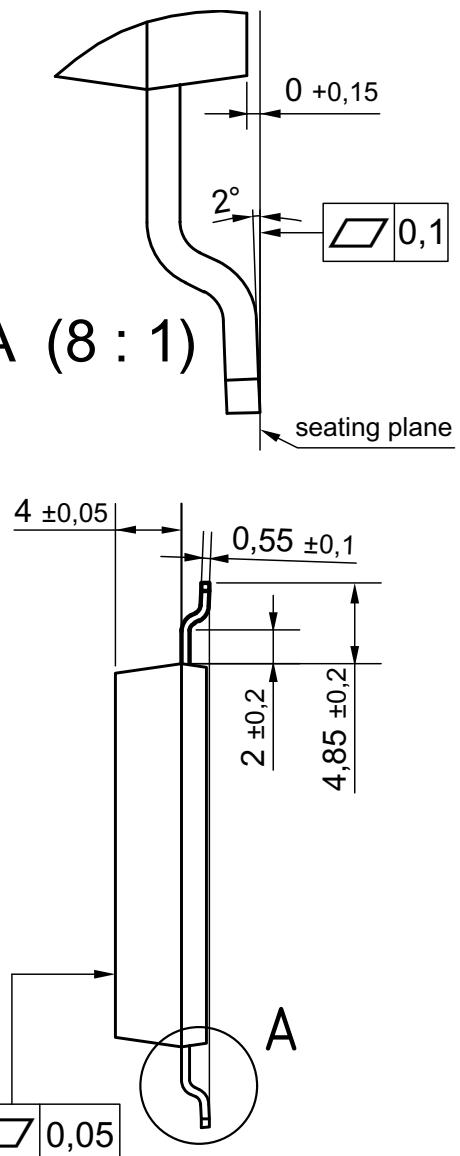
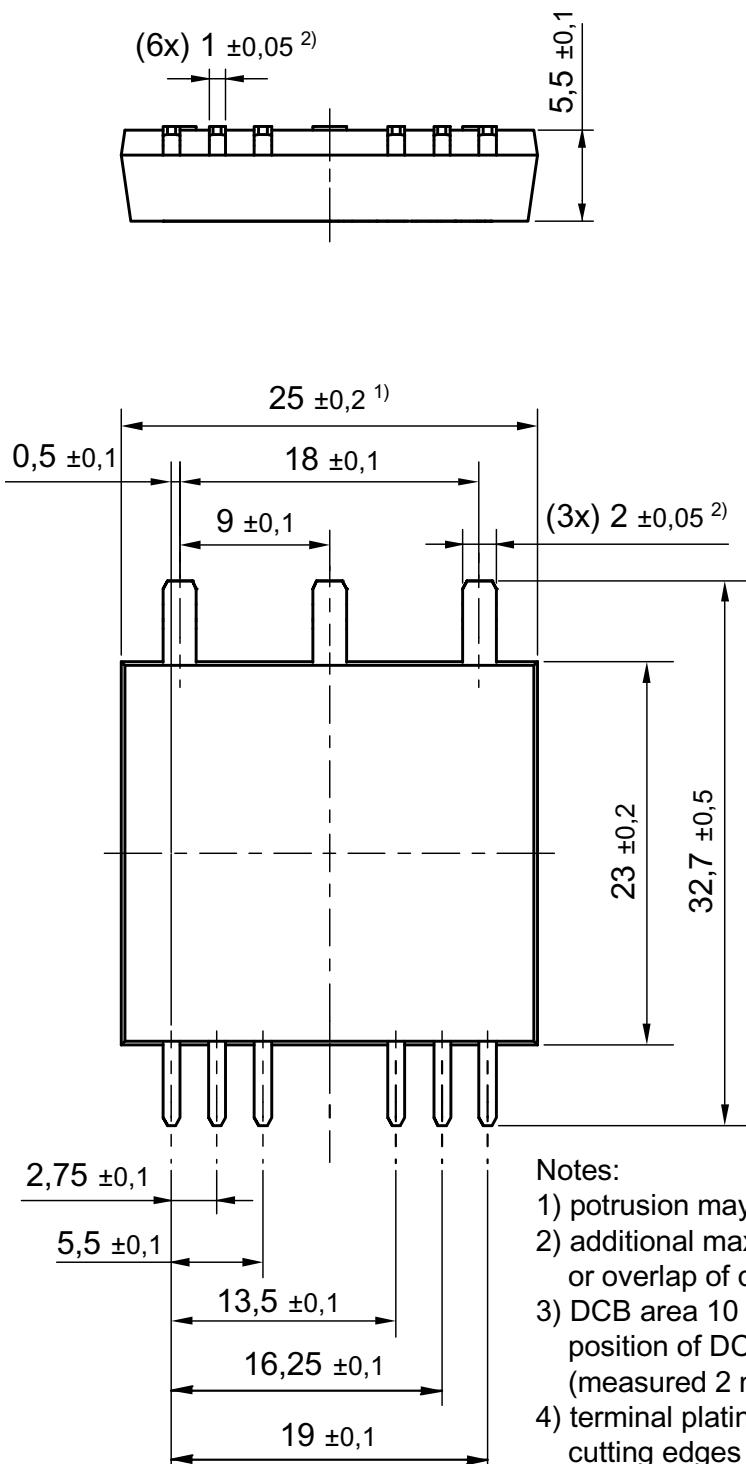
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C _P	coupling capacity between shorted pins and backside metal		90	pF
d _S , d _A	pin - pin	1.65		mm
d _S , d _A	pin - backside metal	4		mm
CTI		400		
Weight			8	g

Ordering	Ordering Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	IXA 40PG1200DHGLB	IXA40PG1200DHGLB	Tape&Reel	200	tbd

IXYS reserves the right to change limits, test conditions and dimensions.

20120131b

Dimensions in mm (1 mm = 0.0394")



Notes:

- 1) protrusion may add 0.2 mm max. on each side
 - 2) additional max. 0.05 mm per side by punching misalignment or overlap of dam bar or bending compression
 - 3) DCB area 10 to 50 µm convex;
position of DCB area in relation to plastic rim: $\pm 25 \mu\text{m}$
(measured 2 mm from Cu rim)
 - 4) terminal plating: 0.2 - 1 µm Ni + 10 - 25 µm Sn (gal v.)
cutting edges may be partially free of plating



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